

HD3SS213 5.4-Gbps DisplayPort 1.2a 2:1 and 1:2 Differential Switch

1 Features

- Compatible with DisplayPort 1.2 electrical standard
- 2:1 and 1:2 switching supporting data rates up to 5.4 Gbps
- Supports HPD switching
- Supports AUX and DDC switching
- Wide -3-dB differential BW of over 5.4 GHz
- Excellent dynamic characteristics (at 2.7 GHz):
 - Crosstalk = -50 dB
 - Isolation = -25 dB
 - Insertion loss = -1.5 dB
 - Return loss = -13 dB
 - Maximum bit-bit skew = 5 ps
- V_{DD} Operating range: 3.3 V ±10%
- Package Options:
 - 5 mm × 5 mm, 50-Pin nFBGA
- Output enable (OE) pin disables switch to save
- HD3SS213 < 10 mW (standby < 30 μW when OE = L)

2 Applications

- PC & notebooks
- **Tablets**
- Connected peripherals & printers

3 Description

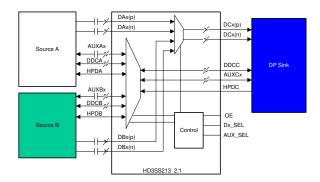
The HD3SS213 device is a high-speed passive switch capable of switching two full DisplayPort 4 lane ports from one of two sources to one target location in an application. It also switches one source to one of two sinks. For DisplayPort applications, the HD3SS213 supports switching of the Auxiliary (AUX), Display Data Channel (DDC), and Hot Plug Detect (HPD) signals in the ZEQ package.

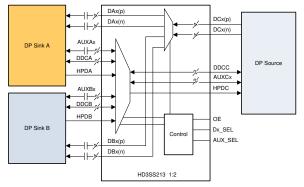
One typical application is a mother board that includes two GPUs that need to drive one DisplayPort sink. The GPU is selected by the Dx SEL pin. Another application is when one source needs to switch between one of two sinks which the example is a side connector and a docking station connector. The switching is controlled using the Dx SEL and AUX SEL pins. The HD3SS213 operates from a single supply voltage of 3.3 V over the full industrial temperature range of -40°C to 105°C.

Device Information (1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
HD3SS213	nFBGA (50)	5.00 mm x 5.00 mm	

For all available packages, see the orderable addendum at the end of the datasheet.





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HD3SS213 Application Block Diagram



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision B (December 2016) to Revision C (January 2021)	Page
•	NOTE: The device in the MicroStar Jr. BGA packaging were redesigned using a laminate nFBGA pack	age.
	This nFBGA package offers datasheet-equivalent electrical performance. It is also footprint equivalent	to the
	MicroStar Jr. BGA. The new package designator in place of the discontinued package designator will b	е
	updated throughout the datasheet.	1

•	Changed u*jr BGA to nFBGA	1
•	Changed ZQE to ZXH	.3
	Changed u*jr ZQE to nFBGA ZXH. Updated thermal data	
	Changed u*jr BGA to nFBGA1	
	o ,	

Changes from Revision A	September 2013) to Revision B	(December 2016)

Page Added Device Information table, ESD Ratings table, Feature Description section, Device Functional Modes section, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.

......1

Changes from Revision * (September 2013) to Revision A (September 2013)



5 Pin Configuration and Functions

	1	2	3	4	5	6	7	8	9
A	Dx_SEL	VDD		DA0(n)	DA1(n)	DA2(n)		DA3(p)	DA3(n)
В	DC0(n)	DC0(p)	GND	DA0(p)	DA1(p)	DA2(p)	OE	DB0(p)	DB0(n)
С		AUX_SEL						GND	
D	DC1(n)	DC1(p)						DB1(p)	DB1(n)
E	DC2(n)	DC2(p)						DB2(p)	DB2(n)
F	DC3(n)	DC3(p)						DB3(p)	DB3(n)
G		GND						GND	
н	AUXC(n)	AUXC(p)	HPDB	GND	DDCCLK_B	AUXB(p)	GND	DDCCLK_A	AUXA(p)
J	HPDC	HPDA	DDCCLK_C	VDD	DDCDAT_B	AUXB(n)	DDCDAT_C	DDCDAT_A	AUXA(n)

nFBGA 50-Pin ZXH Package Top View

Table 5-1. Pin Functions

	PIN	TYPE(1)	DESCRIPTION ⁽²⁾					
NO.	NAME	IIFE'						
H9, J9	AUXA(p), AUXA(n)	I/O	Port A AUX positive signal Port A AUX negative signal					
H6, J6	AUXB(p), AUXB(n)	I/O	Port B AUX positive signal Port B AUX negative signal					
H2, H1	AUXC(p), AUXC(n)	I/O	Port C AUX positive signal Port C AUX negative signal					
C2	AUX_SEL	I	AUX/DDC selection control pin in conjunction with Dx_SEL Pin					



Table 5-1. Pin Functions (continued)

PIN			The unctions (continued)	
NO.	NAME	TYPE ⁽¹⁾	DESCRIPTION ⁽²⁾	
NA	CADA/B/C	I/O	Port A/B/C cable activity detect	
B4, A4	DA0(p), DA0(n)	I/O	Port A, Channel 0, High speed positive signal Port A, Channel 0, High speed negative signal	
B5, A5	DA1(p), DA1(n)	I/O	Port A, Channel 1, High speed positive signal Port A, Channel 1, High speed negative signal	
B6, A6	DA2(p), DA2(n)	I/O	Port A, Channel 2, High speed positive signal Port A, Channel 2, High speed negative signal	
A8, A9	DA3(p), DA3(n)	I/O	Port A, Channel 3, High speed positive signal Port A, Channel 3, High speed negative signal	
B8, B9	DB0(p), DB0(n)	I/O	Port B, Channel 0, High speed positive signal Port B, Channel 0, High speed negative signal	
D8, D9	DB1(p), DB1(n)	I/O	Port B, Channel 1, High speed positive signal Port B, Channel 1, High speed negative signal	
E8, E9	DB2(p), DB2(n)	I/O	Port B, Channel 2, High speed positive signal Port B, Channel 2, High speed negative signal	
F8, F9	DB3(p), DB3(n)	I/O	Port B, Channel 3, High speed positive signal Port B, Channel 3, High speed negative signal	
B2, B1	DC0(p), DC0(n)	I/O	Port C, Channel 0, High speed positive signal Port C, Channel 0, High speed negative signal	
D2, D1	DC1(p), DC1(n)	I/O	Port C, Channel 1, High speed positive signal Port C, Channel 1, High speed negative signal	
E2, E1	DC2(p), DC2(n)	I/O	Port C, Channel 2, High speed positive signal Port C, Channel 2, High speed negative signal	
F2, F1	DC3(p), DC3(n)	I/O	Port C, Channel 3, High speed positive signal Port C, Channel 3, High speed negative signal	
H8, J8	DDCCLK_A, DDCDAT_A	I/O	Port A DDC clock signal Port A DDC data signal	
H5, J5	DDCCLK_B, DDCDAT_B	I/O	Port B DDC clock signal Port B DDC data signal	
J3, J7	DDCCLK_C, DDCDAT_C	I/O	Port C DDC clock signal Port C DDC data signal	
A1	Dx_SEL	I	High speed port selection control pins	
B3, C8, G2, G8, H4, H7	GND	S	Ground	
J2	HPDA	I/O	Port A hot plug detect	
H3	HPDB	I/O	Port B hot plug detect	
J1	HPDC	I/O	Port C hot plug detect	
В7	OE	I	Output enable: OE = V _{IH} : Normal operation OE = V _{IL} : Standby mode	
A2, J4	VDD	S	3.3-V positive power supply voltage	

⁽¹⁾ I = Input, O = Output, S = Supply

⁽²⁾ The high speed data ports incorporate 20-kΩ pulldown resistors that are switched in when a port is not selected and switched out when the port is selected.



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT	
Supply voltage, V _{DD} ⁽²⁾		-0.5	4	V	
Voltage	Differential I/O	-0.5	4	V	
voltage	Control pin	-0.5	V _{DD} + 0.5	V	
Continuous power dissipation		See Se	ection 6.4		
Operating free-air temperature, T	\	-40	105	°C	
Storage temperature, T _{stg}			150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential voltages, are with respect to network ground terminal.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	\/
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	'

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

Typical values for all parameters are at V_{CC} = 3.3 V and T_A = 25°C (unless otherwise noted). All temperature limits are specified by design.

	PARAMETER	TEST CONDITIONS	MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage		3	3.3	3.6	V
V _{IH}	Input high voltage	Control pins and signal pins (Dx_SEL, AUX_SEL, OE, HPDx)	2		V_{DD}	V
V _{IM}	Input mid level voltage	AUX_SEL pin	V _{DD} /2 - 300 mV	V _{DD} /2	V _{DD} /2 + 300 mV	V
V _{IL}	Input low voltage	Control pins and signal pins (Dx_SEL, AUX_SEL, OE, HPDx)	-0.1		0.8	V
V _{I/O_Diff}	Differential voltage (Dx, AUXx)	Switch I/O differential voltage	0		1.8	V _{PP}
V	Dx switching I/O common- mode voltage	Switch I/O common-mode voltage	0		2	V
V _{I/O_CM}	AUXx switching I/O common- mode voltage	Switch I/O common-mode voltage	0		3.6	V
I _{IH}	Input high current (Dx_SEL, AUX_SEL)	V _{DD} = 3.6 V, V _{IN} = V _{DD}			1	μΑ
I _{IM}	Input mid level current (AUX_SEL)	$V_{DD} = 3.6V, V_{IN} = V_{DD}/2$			1	μΑ
I _{IL}	Input low current (Dx_SEL, AUX_SEL)	V _{DD} = 3.6 V, V _{IN} = GND			1	μΑ
	Leakage current (Dx_SEL, AUX_SEL)	V _{DD} = 3.3 V, V _I = 2 V, OE = 3.3 V			1	μA
I _{LK}	Leakage current (HPDx)	V _{DD} = 3.3 V, V _I = 2 V, OE = 3.3 V, Dx_SEL = 3.3 V			1	μA
	Leanage culletti (HFDX)	V _{DD} = 3.3 V, V _I = 2 V, OE = 3.3 V, Dx_SEL = GND			1	μΑ

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



Typical values for all parameters are at V_{CC} = 3.3 V and T_A = 25°C (unless otherwise noted). All temperature limits are specified by design.

	PARAMETER	TEST CONDITIONS	MIN	NOM	MAX	UNIT
I _{off}	Device shut down current	V _{DD} = 3.6 V, OE = GND			2.5	μA
I _{DD}	Supply current	V _{DD} = 3.6 V, Dx_SEL or AUX_SEL = V _{DD} or GND		0.6	1	mA
DA, DB, D	C HIGH SPEED SIGNAL PATH					
C _{ON}	Outputs ON capacitance	V _I = 0 V, outputs open, switch ON		1.5		pF
C _{OFF}	Outputs OFF capacitance	V _I = 0 V, outputs open, switch OFF		1		pF
R _{ON}	ON resistance	V _{DD} = 3.3 V, VCM = 0.5 V to 1.5 V, I _O = -40 mA		8	12	Ω
ΔR _{ON}	ON resistance match between pairs of the same channel	$V_{DD} = 3.3 \text{ V}, 0.5 \text{ V} \le V_{I} \le 1.2 \text{V},$ $I_{O} = -40 \text{ mA}$			1.5	Ω
R _{FLAT_ON}	ON resistance flatness, R _{ON(max)} – R _{ON(min)}	$V_{DD} = 3.3 \text{ V}, 0.5 \text{ V} \le V_1 \le 1.2 \text{ V}$		1.3		Ω
AUXx, DD	C SIGNAL PATH					
C _{ON}	Outputs ON capacitance	V _I = 0 V, outputs open, switch ON		9		pF
C _{OFF}	Outputs OFF capacitance	V _I = 0 V, outputs open, switch OFF		3		pF
R _{ON(AUX)}	ON resistance	$V_{DD} = 3.3 \text{ V}, V_{CM} = 0 \text{ V} - V_{DD}, I_{O} = -8 \text{ mA}$		6	10	Ω
R _{ON(DDC)}	ON resistance on DDC channel	$V_{DD} = 3.3 \text{ V}, V_{CM} = 0.4 \text{ V}, I_{O} = -3 \text{ mA}$		20	30	Ω

6.4 Thermal Information

		HD3SS213	
	THERMAL METRIC	nFBGA (ZXH)	UNIT
		50 PIN	
R _{θJA}	Junction-to-ambient thermal resistance	72.9	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	35.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.1	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	1.6	°C/W
ΨЈВ	Junction-to-board characterization parameter	42.9	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	_	°C/W

6.5 Electrical Characteristics

over recommended operating conditions; R_L and R_{SC} = 50 Ω (unless otherwise noted)⁽¹⁾

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Rı	Dx differential return loss	1.35 GHz		-17		dB
INL	DX differential return loss	2.7 GHz		-13		ub
X _{TALK}	Dx differential crosstalk	2.7 GHz		-50		dB
O _{IRR}	Dx differential off-isolation	2.7 GHz		-25		dB
I.	Dx differential insertion loss	f = 1.35 GHz		-1		dB
'L		f = 2.7 GHz			l db	
	AUX –3-dB bandwidth			360		MHz

(1) For return loss, crosstalk, off-isolation, and insertion loss values, the data was collected on a Rogers material board with minimum length traces on the input and output of the device under test.

Product Folder Links: HD3SS213



6.6 Timing Requirements

over recommended operating conditions; R_L and R_{SC} = 50 Ω (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PD}	Switch propagation delay	R_{SC} and R_L = 50 Ω , see Figure 6-2			100	ps
T _{on}	Dx_SEL/AUX_SEL-to-switch Ton (Data, AUX and DDC)	R_{SC} and R_L = 50 Ω , see Figure 6-1		0.7	1	μs
T _{off}	Dx_SEL/AUX_SEL-to-switch Toff (Data, AUX and DDC)	R_{SC} and R_L = 50 Ω , see Figure 6-1		0.7	1	μs
T _{on}	Dx_SEL/AUX_SEL-to-switch Ton (HPD)	$R_L = 50 \Omega$, see Figure 6-1		0.7	1	μs
T _{off}	Dx_SEL/AUX_SEL-to-switch Toff (HPD)	R_L = 50 Ω, see Figure 6-1		0.7	1	μs
T _{SK(O)}	Inter-pair output skew (CH-CH)	R_{SC} and R_L = 1 k Ω , see Figure 6-2			50	ps
T _{SK(b-b)}	Intra-pair output skew (bit-bit)	R_{SC} and R_L = 1 k Ω , see Figure 6-2		1	5	ps

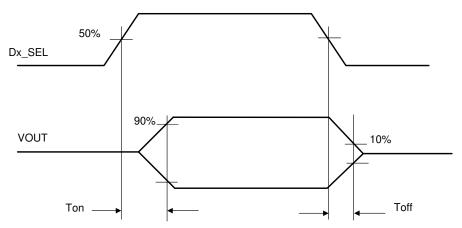
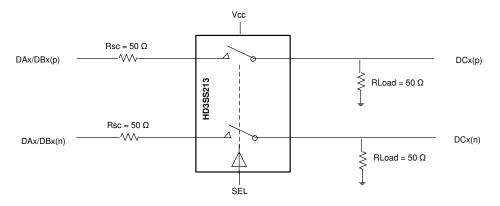
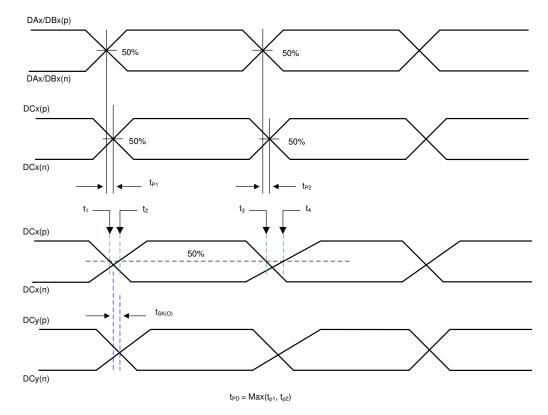


Figure 6-1. Select to Switch Ton and Toff





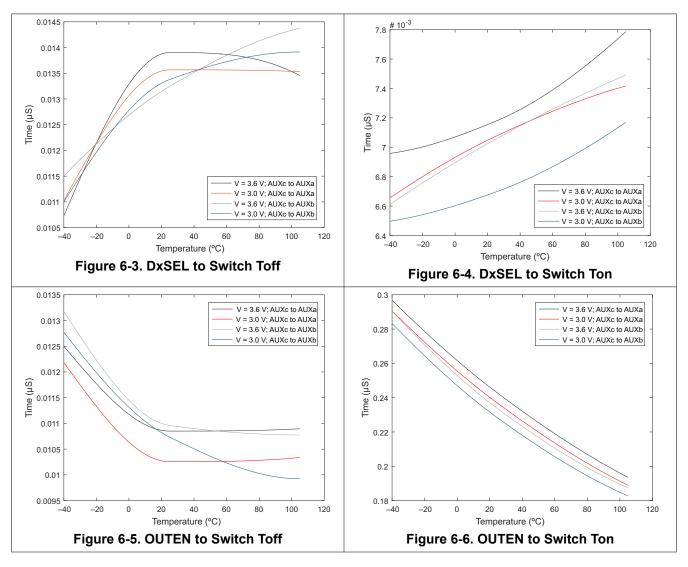


 $t_{\text{SK(O)}}\!=\!$ Difference between t_{PD} for any two pairs of outputs

Figure 6-2. Propagation Delay and Skew



6.7 Typical Characteristics





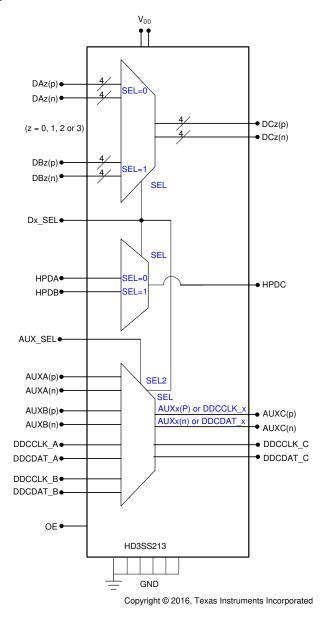
7 Detailed Description

7.1 Overview

The HD3SS213 device is a high-speed passive switch offered in an industry standard 50-pin nFBGA package. The device is specified to operate from a single supply voltage of 3.3 V over the industrial temperature range of -40°C to 105°C. The HD3SS213 is a generic 4-CH high-speed mux/demux type of switch that can be used for routing high-speed signals between two different locations on a circuit board. The HD3SS213 also supports several other high speed data protocols with a differential amplitude of < 1800 mV_{PP} and a common-mode voltage of < 2 V, as with USB 3.0 and DisplayPort 1.2. For display port applications, the HD3SS213 also supports switching of both the auxiliary and hot plug detect signals.

The high speed port selection control inputs of the device, Dx_SEL and AUX_SEL pins can easily be controlled by available GPIO pins within a system.

7.2 Functional Block Diagram



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7.3 Feature Description

The HD3SS213 behaves as a two to one or one to two using high bandwidth pass gates (see *Section 7.2*). The input ports are selected using the AUX SEL and Dx SEL pins which are shown in Table 7-1.

Table 7-1. AUX/DDC Switch Control Logic

CONTROL L	INES	SWITCHED I/O PINS										
AUX_SEL Dx_SEL AUXA		AUXA AUXB		AUXC	DDCA	DDCB	DDCC					
L	L	To/From AUXC	Z	To/From AUXA	Z	Z	Z					
L	Н	Z	To/From AUXC	To/From AUXB	Z	Z	Z					
Н	L	Z	Z	To/From DDCA	To/From AUXC	Z	Z					
Н	Н	Z	Z	To/From DDCB	Z	To/From AUXC	Z					
М	L	To/From AUXC	Z	To/From AUXA	To/From DDCC	Z	To/From DDCA					
М	Н	Z	To/From AUXC	To/From AUXB	Z	To/From DDCC	To/From DDCB					

7.4 Device Functional Modes

The HD3SS213 can be operated in normal operation mode or in shut down mode. In normal operation, the inputs ports of the HD3SS213 are routed to the output ports according to Table 7-1. In standby mode, the HD3SS213 is disabled to enable power savings with a typical current consumption of 2.5 μ A. The functional mode is selected through the OE input pin with HIGH for normal operation and LOW for standby.



8 Application and Implementation

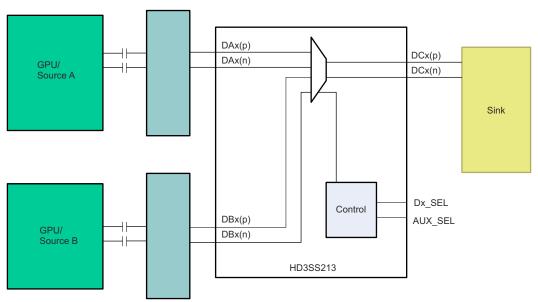
Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

Many interfaces require AC coupling between the source and sink. The 0402 capacitors are the preferred option to provide AC coupling, and the 0603 size capacitors also work. The 0805 size capacitors and C-packs must be avoided. When placing AC coupling capacitors symmetric placement is best. A capacitor value of 0.1 μ F is best and the value must be match for the \pm signal pair. There are several placement options for the AC coupling capacitors. Because the switch requires a bias voltage, the capacitors must only be placed on one side of the switch. If they are placed on both sides of the switch, a biasing voltage must be provided. A few placement options are shown below.

In Figure 8-1, the coupling capacitors are placed on the source pair. In this situation, the switch is biased by the sink.



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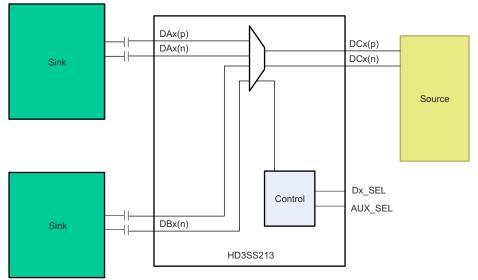
Figure 8-1. Source Biased by the Sink

In Figure 8-2, the coupling capacitors are placed between the switch and Sink. In this situation, the switch is biased by the Source

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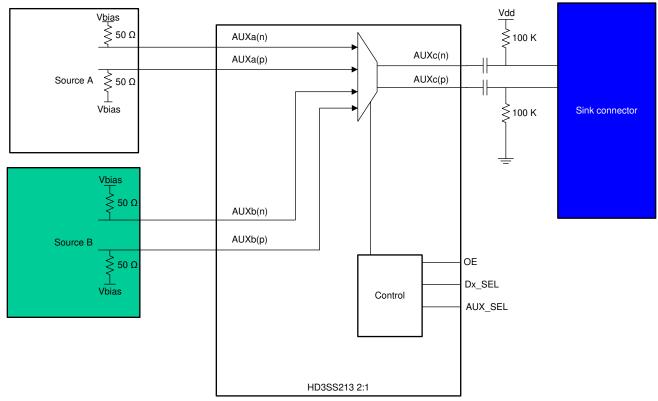


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Figure 8-2. Switch Biased by the Source

8.2 Typical Applications

8.2.1 HD3SS213 AUX Channel in 2:1 Application



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Figure 8-3. HD3SS213 AUX Channel in 2:1 Application Schematic

8.2.1.1 Design Requirements

Table 8-1 lists the design parameters.



Table 8-1. Design Parameters

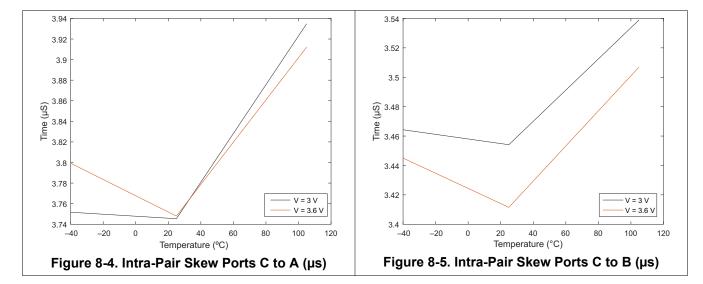
PARAMETERS	VALUE			
Input voltage	3.3 V			
Decoupling capacitors	0.1 μF			
AC capacitors ⁽¹⁾	75 nF to 200 nF AC capacitors			

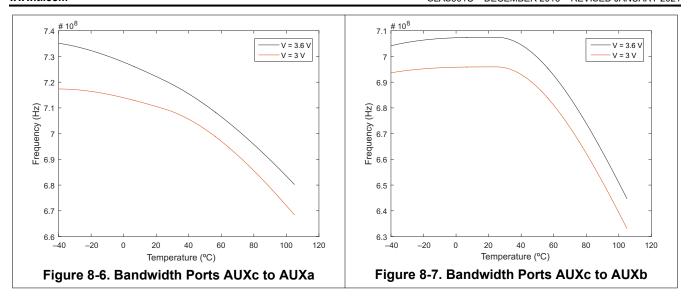
⁽¹⁾ DAx, AUXAx, AUXBx and DBx require AC capacitors. N lines require AC capacitors. Alternate mode signals may or may not require AC capacitors.

8.2.1.2 Detailed Design Procedure

- Connect VDD and GND pins to the power and ground planes of the printed-circuit board with 0.1-μF bypass capacitor
- Use VDD/2 logic level at AUX_SEL pin
- Use 3.3-V TTL/CMOS logic level at Dx_SEL to connect DAx to DCx
- Use GND logic level at Dx_SEL to connect DBx to DCx
- Use controlled-impedance transmission media for all the differential signals
- Ensure the received complimentary signals are with a differential amplitude of <1800 mV_{PP} and a commonmode voltage of <2 V

8.2.1.3 Application Curves





8.2.2 HD3SS213 AUX Channel in 1:2 Application

AUX channel is controlled by AUX_SEL. This pin configures the switch to route the incoming AUX signal to the outgoing AUX path, when AUX_SEL = 0 the AUXA channel is routed to AUXC, when AUX_SEL = 1 the AUXB channel is routed to AUXC.

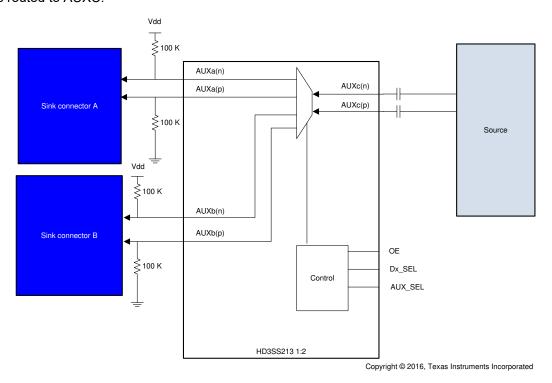


Figure 8-8. HD3SS213 AUX Channel in 1:2 Application Schematic

Power Supply Recommendations

The HD3SS213 requires 3.3 V power sources. 3.3-V supply (VDD) must have 0.1- μ F bypass capacitors to VSS (ground) for proper operation. TI recommends one capacitor for each power terminal. Place the capacitor as close as possible to the terminal on the device and keep trace length to a minimum. Smaller value capacitors like $0.01~\mu$ F are also recommended on the supply terminals.



9 Layout

9.1 Layout Guidelines

- Routing the high-speed differential signal traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects from the DisplayPort connectors to the repeater inputs and from the repeater output to the subsequent receiver circuit.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Decoupling capacitors must be placed next to each power terminal on the HD3SS213. Take care to minimize the stub length of the race connecting the capacitor to the power pin.
- Avoid sharing vias between multiple decoupling capacitors.
- Place vias as close as possible to the decoupling capacitor solder pad.
- Widen VDD and/or GND planes to reduce effect if static and dynamic IR drop.

9.1.1 Differential Traces

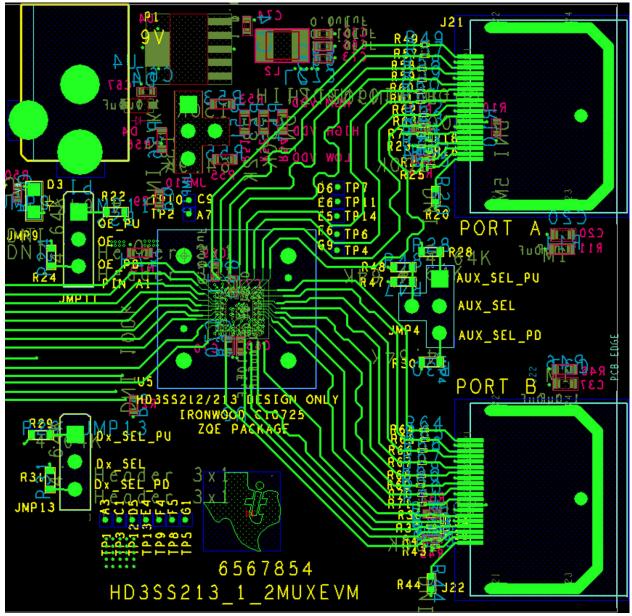
Guidelines for routing PCB traces are necessary when trying to maintain signal integrity and lower EMI. Although there seems to be an endless number of precautions, this section provides only a few main recommendations as layout guidance.

- 1. Reduce intra-pair skew in a differential trace by introducing small meandering corrections at the point of mismatch.
- 2. Reduce inter-pair skew, caused by component placement and IC pinouts, by making larger meandering correction along the signal path. Use chamfered corners with a length-to-trace width ratio of between 3 and 5. The distance between bends must be 8 to 10 times the trace width
- 3. Use 45° bends instead of right-angle (90°) bends. Right-angle bends increase the effective trace width, which changes the differential trace impedance creating large discontinuities. A 45° bends is seen as a smaller discontinuity.
- 4. When routing around an object, route both trace of a pair in parallel. Splitting the traces changes the line-to-line spacing, thus causing the differential impedance to change and discontinuities to occur
- 5. Place passive components within the signal path, such as source-matching resistors or AC coupling capacitors, next to each other. Routing as in case a) creates wider trace spacing than in b). However, the resulting discontinuity is limited to a far narrower area.
- 6. When routing traces next to a via or between an array of vias, make sure that the via clearance section does not interrupt the path of the return current on the ground plane below
- 7. Avoid metal layers and traces underneath or between the pads off the DisplayPort connectors for better impedance matching. Otherwise, they cause the differential impedance to drop below 75 Ω and fail the board during TDR testing.
- 8. Use the smallest size possible for signal trace vias and DisplayPort connector pads as they have less impact on the 100 Ω differential impedance. Large vias and pads can cause the impedance to drop below 85 Ω .
- 9. Use solid power and ground planes for 100 Ω impedance control and minimum power noise.
- 10.For 100 Ω differential impedance use the smallest trace spacing possible, which is usually specified by the PCB vendor.
- 11. Keep the trace length between the DisplayPort connector and the DisplayPort device as short as possible to minimize attenuation.
- 12.Use good DisplayPort connectors whose impedances meet the specifications.
- 13. Place bulk capacitors (for example, 10 μ F) close to power sources, such as voltage regulators or where the power is supplied to the PCB.
- 14.Place smaller 0.1-μF or 0.01-μF capacitors at the device.

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9.2 Layout Example



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Figure 9-1. HD3SS213 Layout Example



10 Device and Documentation Support

10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
HD3SS213ZXHR	Active	Production	NFBGA (ZXH) 50	2500 LARGE T&R	Yes	SNAGCU	Level-3-260C-168 HR	-40 to 105	HD3SS213
HD3SS213ZXHR.B	Active	Production	NFBGA (ZXH) 50	2500 LARGE T&R	Yes	SNAGCU	Level-3-260C-168 HR	-40 to 105	HD3SS213

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
HD3SS213ZXHR	NFBGA	ZXH	50	2500	330.0	12.4	5.3	5.3	1.5	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

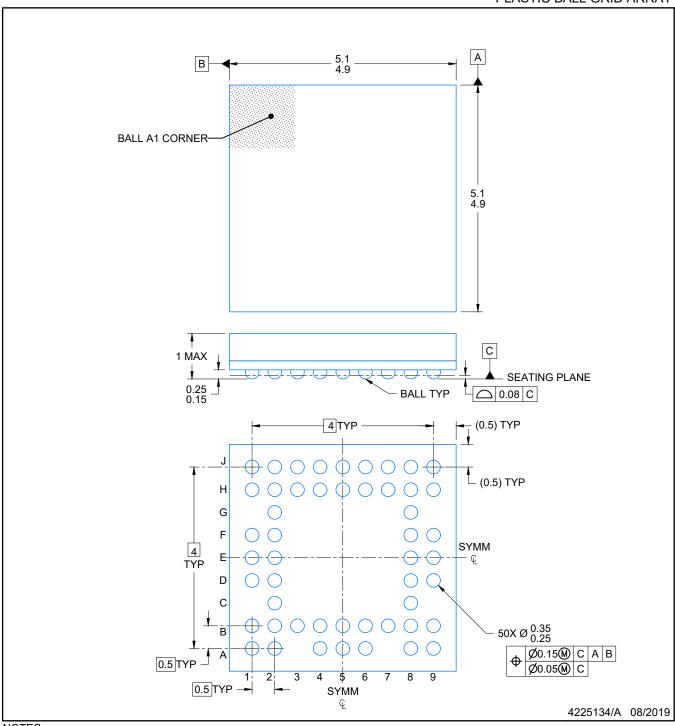
www.ti.com 29-Mar-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
HD3SS213ZXHR	NFBGA	ZXH	50	2500	336.6	336.6	31.8	

PLASTIC BALL GRID ARRAY



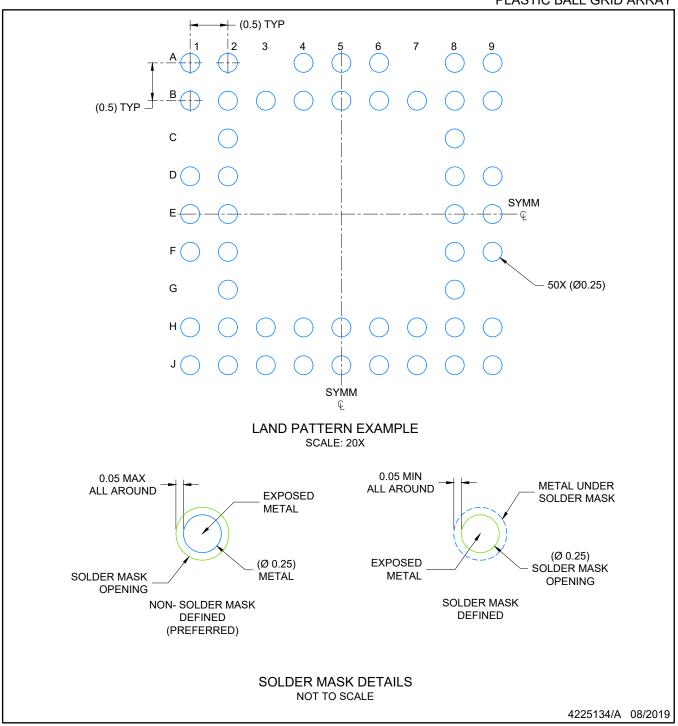
NOTES:

NanoFree is a trademark of Texas Instruments.

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



PLASTIC BALL GRID ARRAY

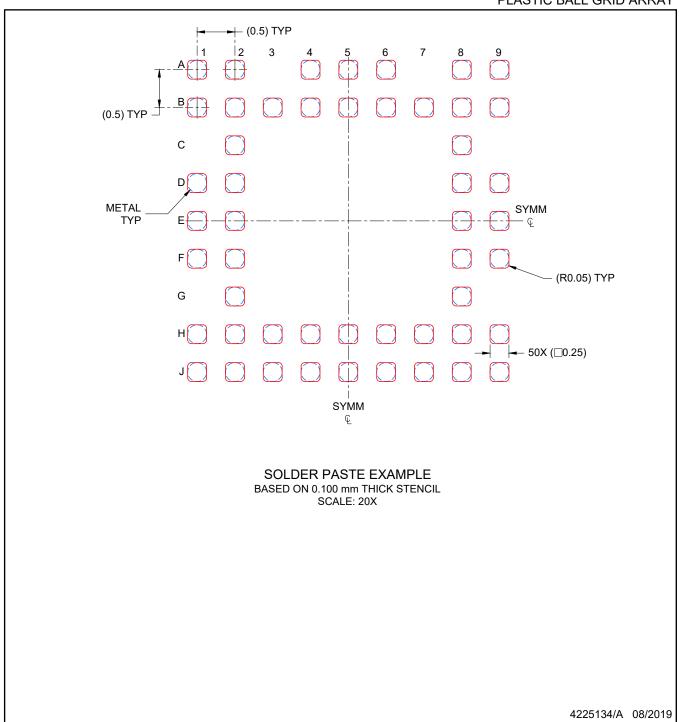


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. Refer to Texas Instruments Literature number SNVA009 (www.ti.com/lit/snva009).



PLASTIC BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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